



PTO/SB/08A (10-01)
Approved for use through 10/31/2002. OMB 0651-0031
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known			
		Application Number	10/736,617		
		Filing Date	December 17, 2003		
		First Named Inventor	Kristy A. Campbell		
		Art Unit	2825-2829		
		Examiner Name	R. Rocchegiani		
Sheet	1	of	5	Attorney Docket Number	M4065.0698/P698-A

U.S. PATENT DOCUMENTS					
Exami ner Initials*	Cite No.†	Document Number Number-Kind Code* (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
V4	**AA	2002/0072188	6/13/2002	Gilton	
↑	**AB	2002/0106849	08/08/2002	Moore	
	**AC	2002/0123169	09/05/2002	Moore et al.	
	**AH	2002/0123248	09/05/2002	Moore et al.	
	**AI	2002/0132417	09/09/2002	Li	
	**AJ	2002/0160551	10/31/2002	Harshfield	
	**AK	2002/0168852	11/14/2002	Harshfield et al.	
	**AL	2002/0190289	12/19/2002	Harshfield et al.	
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	**AM	2003/0043631	03/06/2003	Gilton et al.	
	**AN	2003/0045049	03/06/2003	Campbell et al.	
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	**AQ	2003/0047772	03/13/2003	Li	
	**AR	2003/0047773	03/13/2003	Li	
	**AS	2003/0048519	03/13/2003	Kozicki	
	**AT	2003/0048744	3/2003	Ovshinsky et al.	
	**AU	2003/0049912	03/13/2003	Campbell et al.	
	**AV	2003/0068861	04/10/2003	Li	
	**AW	2003/0068862	04/10/2003	Li	
	**AX	2003/0095426	05/22/2003	Hush et al.	
	**AY	2003/0096497	05/22/2003	Moore et al.	
	**AZ	2003/0107105	06/12/2003	Kozicki	
	**AA1	2003/0117831	06/26/2003	Hush	
	**AB1	2003/0128612	07/10/2003	Moore et al.	
	**AC1	2003/0137869	07/24/2003	Kozicki	
	**AD1	2003/0143782	07/31/2003	Gilton et al.	
	**AE1	2003/0155589	08/21/2003	Campbell et al.	
	**AF1	2003/0155606	08/21/2003	Campbell et al.	
	**AG1	2003/0156447	08/21/2003	Kozicki	
	**AH1	2003/0156463	08/21/2003	Casper et al.	
	**AI1	2003/0209728	11/13/2003	Kozicki et al.	
	**AJ1	2003/0209971	11/13/2003	Kozicki et al.	
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	**AL1	2003/0212724	11/2003	Ovshinsky et al.	
	**AM1	2003/0212725	11/2003	Ovshinsky et al.	
	**AN1	2004/0035401	2/2004	Ramachandran et al.	
	**AO1	3,271,591	9/1966	Ovshinsky	
	**AP1	3,622,319	11/1971	Sharp	
	**AQ1	3,743,847	7/1973	Boland	
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V4	**AS1	3,966,317	6/1976	Wacks et al.	
	**AT1	3,983,542	11/1976	Ovshinsky	

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			Art Unit	2825 2829	
			Examiner Name	R. Recchegiani V4 esher	
Sheet	2	of	5	Attorney Docket Number	M4065.0698/P698-A

V4	**AU1	3,988,720	10/1976	Ovshinsky	
↑	**AV1	4,177,474	12/1979	Ovshinsky	
	**AW1	4,267,261	5/1981	Hallman et al.	
	**AX1	4,269,935	5/1981	Masters et al.	
	**AY1	4,312,938	1/1982	Drexler, et al.	
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	**AK2	4,678,679	7/1987	Ovshinsky	
	**AL2	4,696,758	9/1987	Ovshinsky et al.	
	**AM2	4,698,234	10/1987	Ovshinsky et al.	
	**AN2	4,710,899	12/1987	Young et al.	
	**AO2	4,728,406	3/1988	Banerjee et al.	
	**AP2	4,737,379	4/1988	Hudgens et al.	
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	**AZ2	4,847,674	7/1989	Sliwa et al.	
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		Filing Date	December 17, 2003		
		First Named Inventor	Kristy A. Campbell		
		Art Unit	2825-2829		
		Examiner Name	R. Rocchegiani ✓		
Sheet	3	of	5	Attorney Docket Number	M4065.0698/P698-A

✓	**AR3	5,512,328	4/1996	Yoshimura et al.	
↑	**AS3	5,512,773	4/1996	Wolf et al.	
	**AT3	5,534,711	7/1996	Ovshinsky et al.	
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	**AX3	5,591,501	1/1997	Ovshinsky et al.	
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	**AB4	5,714,768	2/1998	Ovshinsky et al.	
	**AC4	5,726,083	3/1998	Takaishi	
	**AD4	5,789,277	8/1998	Zahorik et al.	
	**AE4	5,814,527	9/29/1998	Wolstenholme et al	
	**AF4	5,818,749	10/06/1998	Harshfield	
	**AG4	5,825,046	10/1998	Czubatyj et al.	
	**AH4	5,841,150	11/1998	Gonzalez et al.	
	**AI4	5,846,889	12/1998	Harbison et al.	
	**AJ4	5,851,882	12/22/1998	Harshfield	
	**AK4	5,869,843	2/9/1999	Harshfield	
	**AL4	5,896,312	4/20/1999	Kozicki et al.	
	**AM4	5,912,839	6/1999	Ovshinsky et al.	
	**AN4	5,914,893	6/22/1999	Kozicki et al.	
	**AO4	5,933,365	8/1999	Klersy et al.	
	**AP4	5,998,066	12/1999	Block et al.	
	**AQ4	6,011,757	1/2000	Ovshinsky	
	**AR4	6,031,287	2/29/2000	Harshfield	
	**AS4	6,077,729	6/2000	Harshfield	
	**AT4	6,084,796	7/4/2000	Kozicki et al.	
	**AU4	6,087,674	7/2000	Ovshinsky et al.	
	**AV4	6,141,241	10/2000	Ovshinsky et al.	
	**AW4	6,177,338	1/2001	Liaw et al.	
	**AX4	6,117,720	9/2000	Harshfield	
	**AY4	6,143,604	11/2000	Chiang et al.	
	**AZ4	6,236,059	5/2001	Wolsteinholme et al.	
	**AA5	6,274,805	08/2001	Nakazawa et al.	
	**AB5	6,297,170	10/2001	Gabriel et al.	
	**AC5	6,300,684	10/2001	Gonzalez et al.	
	**AD5	6,316,784	11/2001	Zahorik et al.	
	**AE5	6,329,606	12/2001	Freyman et al.	
	**AF5	6,339,544	1/2002	Chiang et al.	
	**AG5	6,348,365	2/19/2002	Moore et al.	
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	**AI5	6,376,284	4/2002	Gonzalez et al.	
	**AJ5	6,391,688	5/2002	Gonzalez et al.	
	**AK5	6,404,665	6/2002	Lowery et al.	
	**AL5	6,414,376	7/2002	Thakur et al.	
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✓	**AN5	6,420,725	7/16/2002	Harshfield	

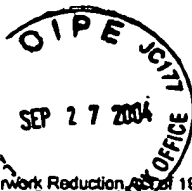
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/736,617
		Filing Date	December 17, 2003
		First Named Inventor	Kristy A. Campbell
		Art Unit	2825 2829
		Examiner Name	R. Rocchegiani V. Yeager
		Attorney Docket Number	M4065.0698/P698-A
Sheet	4	of	5

✓	**AO5	6,423,628	7/2002	Li et al.	
✓	**AP5	6,429,064	8/2002	Wicker	
✓	**AQ5	6,437,383	8/2002	Xu	
✓	**AR5	6,440,837	8/27/2002	Harshfield	
✓	**AS5	6,462,984	10/2002	Xu et al.	
✓	**AT5	6,480,438	11/2002	Park	
✓	**AU5	6,487,113	11/2002	Park et al.	
✓	**AV5	6,501,111	12/2002	Lowery	
✓	**AW5	6,507,061	1/2003	Hudgens et al.	
✓	**AX5	6,511,862	1/2003	Hudgens et al.	
✓	**AY5	6,511,867	1/2003	Lowery et al.	
✓	**AZ5	6,512,241	1/2003	Lai	
✓	**AA6	6,514,805	2/2003	Xu et al.	
✓	**AB6	6,531,373	3/2003	Gill et al.	
✓	**AC6	6,534,781	3/2003	Dennison	
✓	**AD6	6,545,287	4/2003	Chiang	
✓	**AE6	6,545,907	4/2003	Lowery et al.	
✓	**AF6	6,555,860	4/2003	Lowery et al.	
✓	**AG6	6,563,164	5/2003	Lowery et al.	
✓	**AH6	6,566,700	5/2003	Xu	
✓	**AI6	6,567,293	5/2003	Lowery et al.	
✓	**AJ6	6,569,705	5/2003	Chiang et al.	
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✓	**AL6	6,576,921	6/2003	Lowery	
✓	**AM6	6,586,761	7/2003	Lowery	
✓	**AN6	6,589,714	7/2003	Maimon et al.	
✓	**AO6	6,590,807	7/2003	Lowery	
✓	**AP6	6,593,176	7/2003	Dennison	
✓	**AQ6	6,597,009	7/2003	Wicker	
✓	**AR6	6,605,527	8/2003	Dennison et al.	
✓	**AS6	6,613,604	9/2003	Maimon et al.	
✓	**AT6	6,621,095	9/2003	Chiang et al.	
✓	**AU6	6,625,054	9/2003	Lowery et al.	
✓	**AV6	6,638,820	10/2003	Moore	
✓	**AW6	6,642,102	11/2003	Xu	
✓	**AX6	6,646,297	11/2003	Dennison	
✓	**AY6	6,649,928	11/2003	Dennison	
✓	**AZ6	6,667,900	12/2003	Lowery et al.	
✓	**AA7	6,671,710	12/2003	Ovshinsky et al.	
✓	**AB7	6,673,648	1/2004	Lowrey	
✓	**AC7	6,673,700	1/2004	Dennison et al.	
✓	**AD7	6,674,115	1/2004	Hudgens et al.	
✓	**AE7	6,687,427	2/2004	Ramalingam et al.	
✓	**AF7	6,690,026	2/2004	Peterson	
✓	**AG7	6,696,355	2/2004	Dennison	
✓	**AH7	6,687,153	2/2004	Lowery	
✓	**AI7	6,707,712	3/2004	Lowery	
✓	**AJ7	6,714,954	3/2004	Ovshinsky et al.	

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PTO/SB/08A (10-01)

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		Examiner Name	R. Reechegiani		
Sheet	5	of	5	Attorney Docket Number	M4065.0698/P698-A

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ²	Number ³ -Kind Code ⁴ (if known)			
V4	**BA	JP	5-6126916	10/19981	Akira et al.	
V4	**BB	WO	00/48196	08/17/2000	Kozicki et al.	
V4	**BC	WO	02/21542	03/14/2002	Kozicki et al.	

Examiner Signature	V. Y. [Signature]	Date Considered	03/02/05
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Examiner Signature	V. Y. [Signature]	Date Considered	03/02/05
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Application Number		NEW 7			
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First Named Inventor		Kristy A. Campbell			
Art Unit		N/A 2829			
Examiner Name		Not Yet Assigned V-YOR/KOR			
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		Number-Kind Code ² (if known)				
VY	AA	6,473,332		10/2002	Ignatiev et al.	
	AB	4,316,946		1/1982	Masters, et al.	
	AC	4,419,421		12/1983	Wichelhaus, et al.	
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	AQ	2003/0035315		02/20/03	Kozicki	
	AR	US 2002/0168820		11/14/2002	Kozicki et al.	
	AS	6,469,364		10/22/2002	Kozicki	
	AT	6,388,324		05/14/2002	Kozicki et al.	
	AU	US 2002/0000666		01/03/2002	Kozicki et al.	
	AV	5,500,532		03/19/1996	Kozicki et al.	

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		Country Code ³	Number-Kind Code ² (if known)				
VY	BA	WO	97/48032	12/18/1997	Kozicki et al.		
VY	BB	WO	99/28914	06/10/1999	Kozicki et al.		

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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VY	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
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				Application Number	NEW <u>7</u>
				Filing Date	December <u>12</u> , 2003
				First Named Inventor	Kristy A. Campbell
				Art Unit	N/A <u>2829</u>
				Examiner Name	Not Yet Assigned <u>V. Yeung/Kov</u>
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			Filing Date	December 12, 2003	
			First Named Inventor	Kristy A. Campbell	
			Art Unit	N/A 12829	
			Examiner Name	Not Yet Assigned V. Y. Heston	
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			First Named Inventor	Kristy A. Campbell	
			Art Unit	<u>N/A</u> <u>2829</u>	
			Examiner Name	Not Yet Assigned <u>V. J. Jester</u>	
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			Art Unit	N/A 2829	
			Examiner Name	Not Yet Assigned v. 4/18/16	
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Substitute for form 1449A/B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Application Number	NEW 7
				Filing Date	December 12, 2003
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				Art Unit	N/A 2829
				Examiner Name	Not Yet Assigned V402/Kov
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